



### **40V N-Channel Enhancement Mode MOSFET**

Voltage

40 V

Current

40 A

#### **Features**

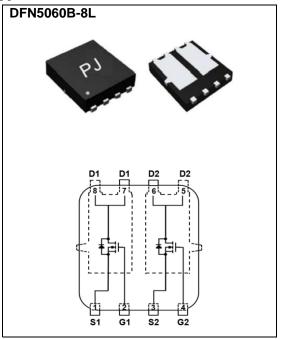
- $R_{DS(ON)}$ ,  $V_{GS}@10V$ ,  $I_{D}@8A<10.5m\Omega$
- $R_{DS(ON)}$ ,  $V_{GS}@4.5V$ ,  $I_{D}@4A<15m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### **Mechanical Data**

• Case: DFN5060B-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0035 ounces, 0.092 grams



### **Maximum Ratings and Thermal Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		$V_{DS}$	40	.,,	
Gate-Source Voltage		$V_{GS}$	<u>+</u> 20	V	
Continuous Drain Current (Note 4)	T <sub>C</sub> =25°C	l <sub>D</sub>	40	А	
	T <sub>C</sub> =100°C		25		
Pulsed Drain Current (Note 1)	T <sub>C</sub> =25°C	I <sub>DM</sub>	120		
Power Dissipation	T <sub>C</sub> =25°C	Po	32	W	
	T <sub>C</sub> =100°C		12		
Continuous Drain Current (Note 4)	T <sub>A</sub> =25°C	I <sub>D</sub>	9.5		
	T <sub>A</sub> =70°C		7.5	Α	
Power Dissipation	T <sub>A</sub> =25°C	Po	1.7	10/	
	T <sub>A</sub> =70°C		1.1	W	
Single Pulse Avalanche Energy (Note 6)		E <sub>AS</sub>	72	mJ	
Operating Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~150	°C	
Typical Thermal Resistance (Note 4,5)	Junction to Case	$R_{ heta JC}$	3.9	°C/W	
	Junction to Ambient	$R_{\theta JA}$	73.5		

Limited only By Maximum Junction Temperature





## **Electrical Characteristics** (T<sub>A</sub>=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	40	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250uA$	1	1.7	2.5		
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =10V, $I_D$ =8A	-	9	10.5	mΩ	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	$V_{GS}$ =4.5V, $I_{D}$ =4A	-	12	15		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =40V, V <sub>GS</sub> =0V	-	-	1	uA	
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	$Q_g$	V <sub>DS</sub> =20V, I <sub>D</sub> =8A, V <sub>GS</sub> =10V <sup>(Note 2,3)</sup>	-	22	-	nC	
Gate-Source Charge	$Q_gs$		-	4.2	-		
Gate-Drain Charge	$Q_{gd}$		-	4.0	-		
Input Capacitance	Ciss	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V,	-	1258	-	pF	
Output Capacitance	Coss		-	134	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	88	-		
Turn-On Delay Time	td <sub>(on)</sub>	\/ 45\/  40	-	13	-		
Turn-On Rise Time	t <sub>r</sub>	$V_{DS}$ =15V, $I_{D}$ =1A, $V_{GS}$ =10V, $R_{G}$ =3.3 $\Omega$ (Note 2,3)	-	14	-	ns	
Turn-Off Delay Time	td <sub>(off)</sub>		-	45	-		
Turn-Off Fall Time	t <sub>f</sub>		-	9	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	40	А	
Diode Forward Current	I <sub>S</sub>						
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> =1A, V <sub>GS</sub> =0V	-	0.7	1	V	

#### NOTES:

- 1. Pulse width<a>300us</a>, Duty cycle<a>2%</a>.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub> =25°C.
- 4. The maximum current rating is package limited.
- 5. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH,  $I_{AS}$ =38A,  $V_{DD}$ =25V,  $V_{GS}$ =10V, Starting  $T_J$ =25°C.
- 7. Guaranteed by design, not subject to production testing.





#### **TYPICAL CHARACTERISTIC CURVES**

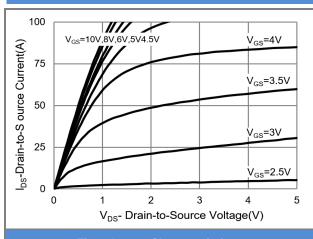


Fig.1 Output Characteristics

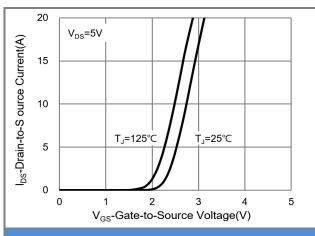


Fig.2 Transfer Characteristics

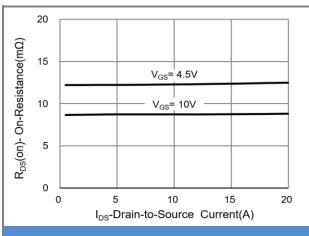


Fig.3 On-Resistance vs. Drain Current

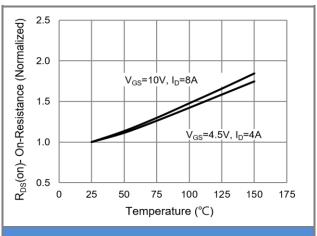


Fig.4 On-Resistance vs. Junction temperature

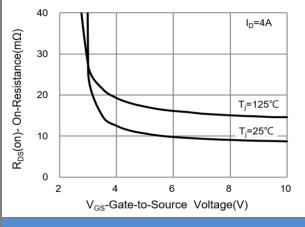


Fig.5 On-Resistance Variation with V<sub>GS</sub>

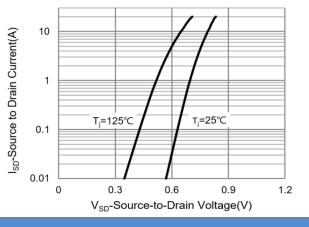
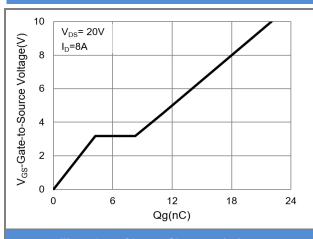


Fig.6 Source-Drain Diode Forward Voltage





### **TYPICAL CHARACTERISTIC CURVES**



**Fig.7 Gate-Charge Characteristics** 

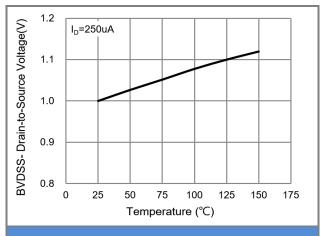


Fig.8 Breakdown Voltage Variation vs. Temperature

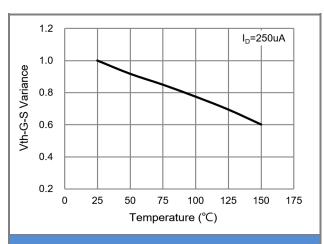


Fig.9 Threshold Voltage Variation with Temperature

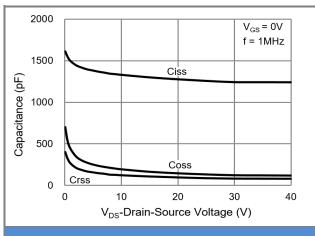


Fig.10 Capacitance vs. Drain-Source Voltage

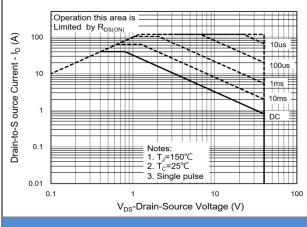


Fig.11 Maximum Safe Operating Area

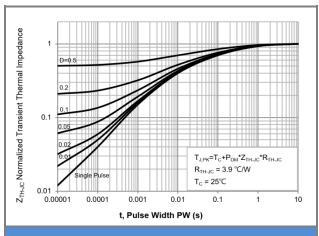


Fig.12 Normalized Transient Thermal Impedance

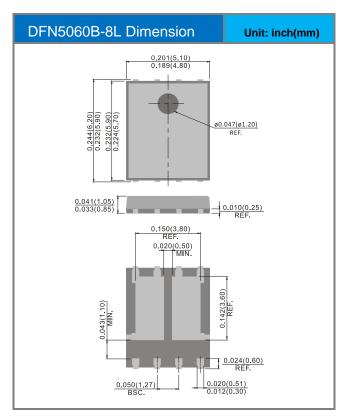


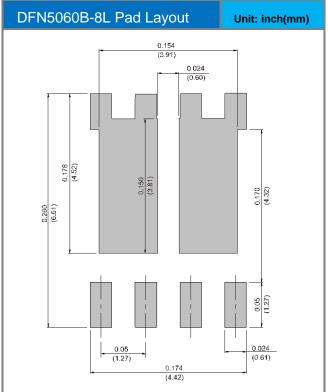


### **Part No Packing Code Version**

Part No Packing Code	Package Type	Packing Type	Marking	Version	
PJQ5846_R2_00001	DFN5060B-8L	3000pcs / 13" reel	Q5846	Halogen free	

### **Packaging Information & Mounting Pad Layout**









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